

Amendments to the Specification:

Please replace the title of the invention with the following amended title:

**IMAGE SENSOR HAVING A REDUCED NUMBER OF WHITE PIXELS
AND A REDUCED FIXED PATTERN NOISE BY POSITIONING THE
SOURCE REGION SUBSTANTIALLY IN THE DOPED REGION OF THE
PHOTOSENSITIVE ELEMENT**

Please substitute the following amended paragraph for the pending paragraph beginning on page 4, line 14:

When the length 18 of the gate 9 of the reset transistor 6 is the same as [[the]] a length 18' of the gate 17 of the source follower transistor 16, the absolute value of the threshold voltage of the reset transistor will be lower than for the source follower transistor. The well of the reset transistor is only partly present below the gate of the reset transistor, so that the concentration of the dopant atoms is lower than below the gate of the source follower transistor. In order to compensate the lower absolute value of the threshold voltage of the reset transistor, the length 18 of the gate 9 of the reset transistor 6 is increased. So it is advantageous to design the length of the gate of the reset transistor longer than the length 18' of the gate 17 of the source follower transistor 16 as shown in FIG. 13.

Please add the following new paragraph at page 7, line 12.

FIG. 13 is a partial cross sectional view of the source follower transistor and the reset transistor.